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April 2012

FJD3305H1 NPN Silicon Transistor

Features

- High Voltage Switch Mode Application
- Fast Speed Switching
- Wide Safe Operating Area
- Suitable for Electronic Ballast Application
- Wave Soldering



1. Base 2. Collector 3. Emitter

Absolute Maximum Ratings* T_C = 25°C unless otherwise noted

Symbol	Parameter	Value	Units
V _{CBO}	Collector-Base Voltage	700	V
V _{CEO}	Collector-Emitter Voltage	400	V
V _{EBO}	Emitter-Base Voltage	9	V
I _C	Collector Current (DC)	4	Α
I _{CP}	Collector Current (Pulse)	8	Α
I_{B}	Base Current	2	Α
P _C	Collector Dissipation, $T_a = 25^{\circ}C$ $T_c = 25^{\circ}C$	1.1 50	W
TJ	Junction Temperature	150	°C
T _{STG}	Storage Temperature	-65 to 150	°C

^{*} These ratings are limiting values above which the serviceability of any semiconductor device may be impaired.

Thermal Characteristics $T_a = 25$ °C unless otherwise noted

Symbol	Parameter	Value	Units
$R_{ heta JA}$	Thermal Resistance, Junction to Ambient	110	°C/W
$R_{ heta Jc}$	Thermal Resistance, Junction to Case	2.0	°C/W

^{*} Device mounted on minimum pad size

Ordering Information

Part Number	Marking	Package	Packing Method	Remarks
FJD3305H1TM	J3305H1	D-PAK	Tape & Reel	

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Electrical Characteristics* $T_C = 25$ °C unless otherwise noted

Symbol	Parameter	Conditions	Min.	Тур.	Max.	Units
BV _{CBO}	Collector-Base Breakdwon Voltage	$I_C = 500 \mu A, I_E = 0$	700			V
BV _{CEO}	Collector-Emitter Breakdown Voltage	$I_C = 5mA, I_B = 0$	400			V
BV _{EBO}	Emitter-Base Breakdown Voltage	$I_E = 500 \mu A, I_C = 0$	9			V
I _{CBO}	Collector Cut-off Current	$V_{CB} = 700V, I_{E} = 0$			1	μΑ
I _{EBO}	Emitter Cut-off Current	$V_{EB} = 9V, I_{C} = 0$			1	μΑ
h _{FE1}	DC Current Gain *	$V_{CE} = 5V, I_{C} = 1A$	19		28	
h _{FE2}		$V_{CE} = 5V, I_{C} = 2A$	8		40	
V _{CE(sat)}	Collector-Emitter Saturation Voltage	$I_C = 1A, I_B = 0.2A$			0.5	V
, ,		$I_C = 2A, I_B = 0.5A$			0.6	V
		$I_C = 4A, I_B = 1A$			1.0	V
V _{BE(sat)}	Base-Emitter Saturation Voltage	$I_C = 1A, I_B = 0.2A$			1.2	V
(,		$I_C = 2A, I_B = 0.5A$			1.6	V
f _T	Current Gain Bandwidth Product	$V_{CE} = 10V, I_{C} = 0.5A$	4			MHz
C _{ob}	Output Capacitance	$V_{CB} = 10V, f = 1MHz$		65		pF
t _{ON}	Turn On Time	$V_{CC} = 125V, I_{C} = 2A$			0.8	μS
t _{STG}	Storage Time	$I_{B1} = -I_{B2} = 0.4A$			4.0	μS
t _F	Fall Time	$R_L = 62.5\Omega$			0.9	μS

^{*} Pulse Test: Pulse Width≤300μs, Duty Cycle≤2%

Typical Performance Characteristics V_{CE} = 5V 4.0 I_B = 300mA Ic [A], COLLECTOR CURRENT 3.5 I_B = 250mA h_{Fe}, DC CURRENT GAIN $I_{B} = 200 \text{m/s}$ 2.5 2.0 $I_B = 50 \text{mA}$ 0.01 $V_{CE}[V]$, COLLECTOR-EMITTER VOLTAGE I_c [A], COLLECTOR CUTRRENT Figure 1. Static Characteristic Figure 2. DC Current Gain $I_c = 4 I_B$ Voe(sat) [V], SATURATION VOLTAGE V_{BE}(sat) [V], SATURATION VOLTAGE Ta = 125 °C I_C [A], COLLECTOR CURRENT I_c [A], COLLECTOR CURRENT Figure 4. Base - EmitterSaturation Voltage Figure 3. Collector- Emitter Saturation Voltage 10000 C t_F & t_{srg} [μs], SWITCHING TIME 1000 CAPACITANCE[pF] 1000 Ta = 125 °C 100 Cob I_c [A], COLLECTOR CURRENT REVERSE VOLTAGE[V] Figure 5. Switching Time Figure 6. Capacitance

Typical Performance Characteristics (Continued)

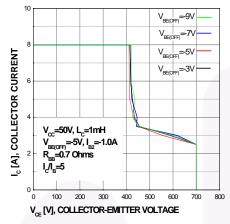


Figure 7. Reverse Biased Safe Operating Area

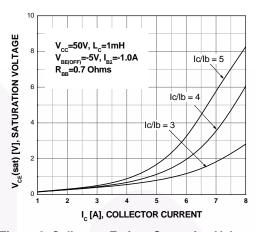


Figure 8. Collector- Emitter Saturation Voltage at RBSOA

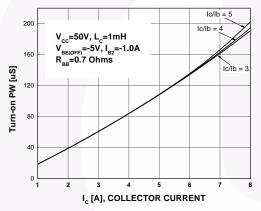


Figure 9. Input Pulse width vs Correct current at RBSOA

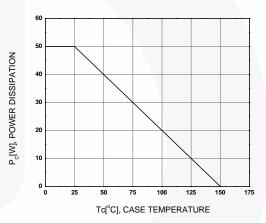


Figure 10. Power Derating

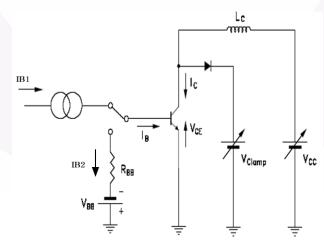
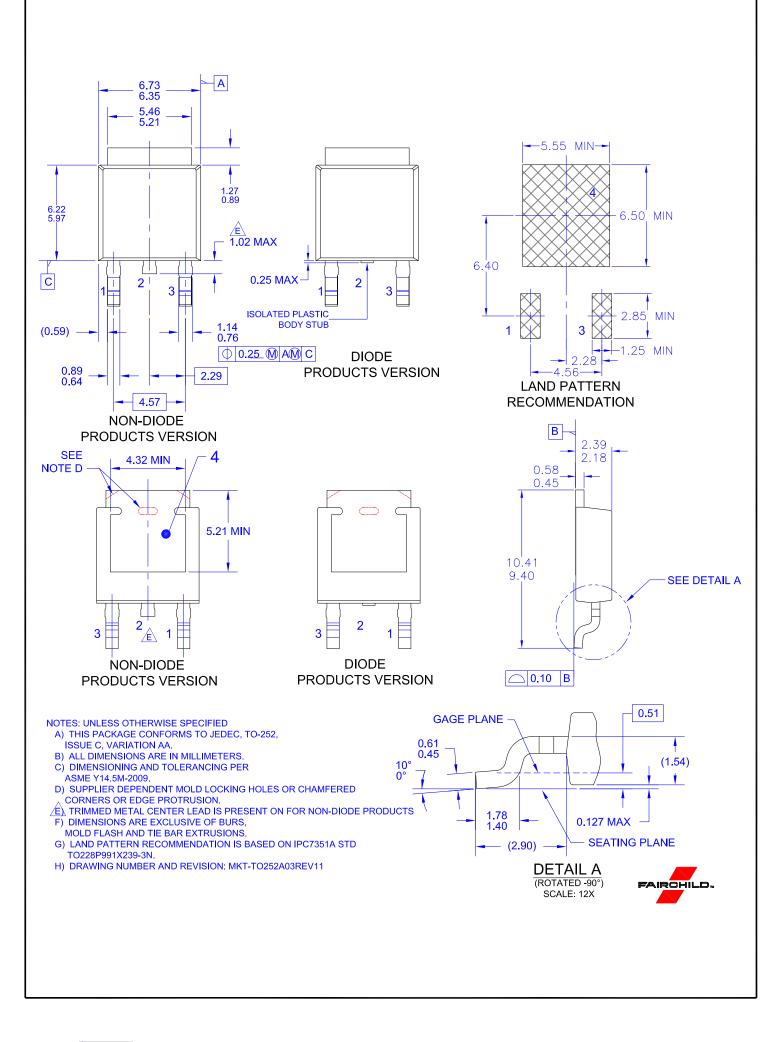


Figure 11. RBSOA Test Circuit



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